Rec'd PET/PTO 16 JAN 2006 10/540599

## Declaration and Power of Attorney For Patent Application

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am an original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled SIALITE BINARY WEB CEMENT, ITS PREPARATION METHOD AND USAGE METHOD (Attorney Docket No. 016687/9004), the specification of which was filed with our authority, on December 24, 2003, as International Application No. PCT/CN2003/001110.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims referred to above.

I acknowledge the duty to disclose to the Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, §1.56.

As a named inventor, I hereby appoint the following registered practitioners associated with the customer number identified below to prosecute this application and transact all business in the Patent and Trademark Office connected therewith; and request that the Office direct all communication in or pertaining to this application to:

Customer Number 23409

I hereby claim foreign priority benefits under Title 35, United States Code, §119 of the foreign application for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application
02158190.8 China 24 December 2002
(Number) (Country) (Day/Month/Year Filed)

The undersigned to this Declaration and Power of Attorney hereby authorize the U.S. attorneys named herein to accept and follow instructions from NTD Patent & Trademark Agency Limited, 10th Floor, Block A, Investment Plaza, 27 Jingrongdajie, Beijing 100032 P.R. China as to any actions to be taken in the U.S. Patent and Trademark Office regarding this application without direct communication between the U.S. attorneys and the undersigned. In the event of a change in the person(s) from whom instructions may be taken, the undersigned will so notify the U.S. attorneys.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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